

09/09/2019

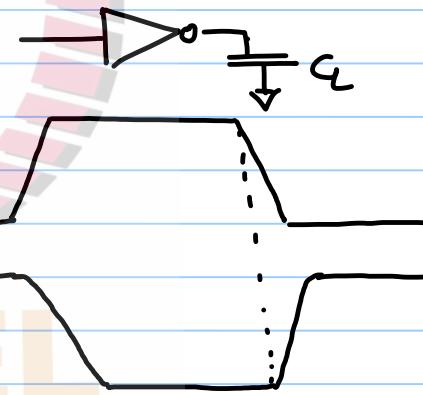
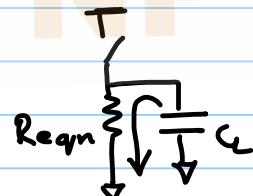
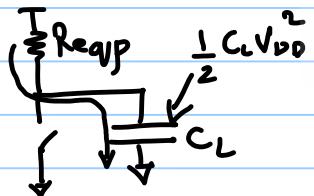
EE5311

MODULE - 3 - THE INVERTER

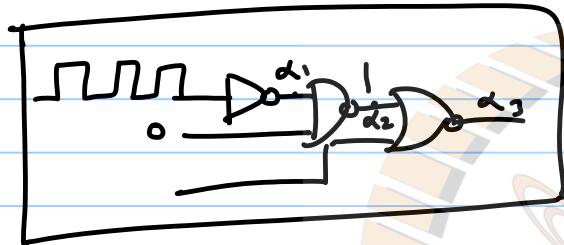
POWER:

- 1) Dynamic power
- 2) Short circuit power
- 3) Leakage power

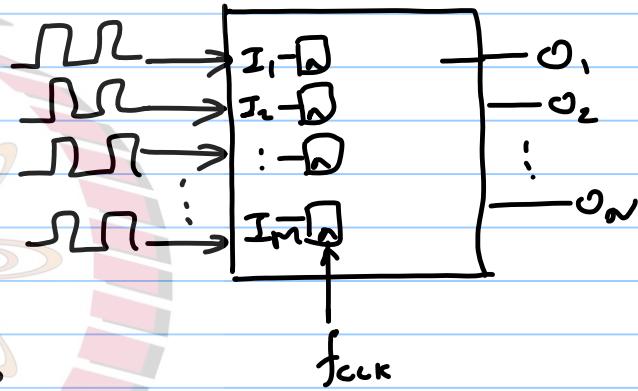
1) Dynamic Power:



FOR EVERY CHARGE/DISCHARGE CYCLE Energy
= $C_L V_{DD}^2 (5V)$



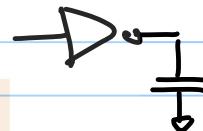
$\alpha \rightarrow$ ACTIVITY FACTOR



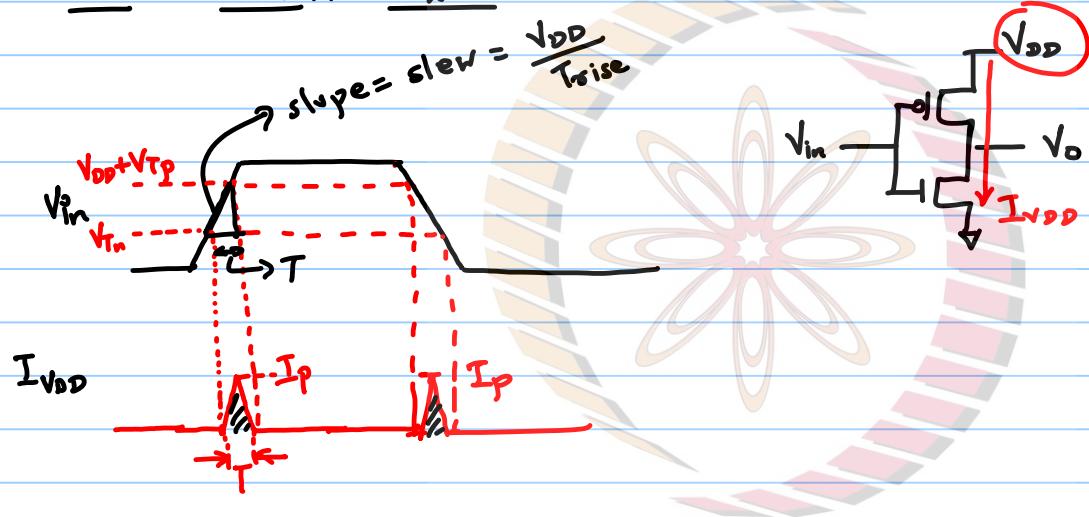
$$\text{AVERAGE ENERGY PER NODE} = \alpha C_L V_{DD}^2$$

$$P_{DYN} = \alpha C_L V_{DD}^2 \cdot f_{CLK}$$

STRONGEST CONTROL



SHORT CIRCUIT POWER



$$E_{SC} = \int_0^T V_{DD} \cdot I_{VDD}(t) dt = \frac{1}{2} V_{DD} \cdot I_p(T) \leftarrow$$

$$\frac{V_{DD}}{T_{rise}} = \frac{V_{DD} + V_{TP} - V_{TN}}{(T)} \Rightarrow T = \frac{(\sqrt{DD} - 2\sqrt{V_{TN}}) \text{trise}}{\sqrt{DD}} \quad (\text{if } V_{TN} = -V_{TP})$$

$$E_{sc} = \sqrt{V_{DD}} \cdot I_p \left(\frac{(V_{DD} - 2V_{Th})}{\sqrt{V_{DD}}} \right) \cdot t_{rise}$$

$$= I_p (V_{DD} - 2V_{Th}) t_{rise}$$

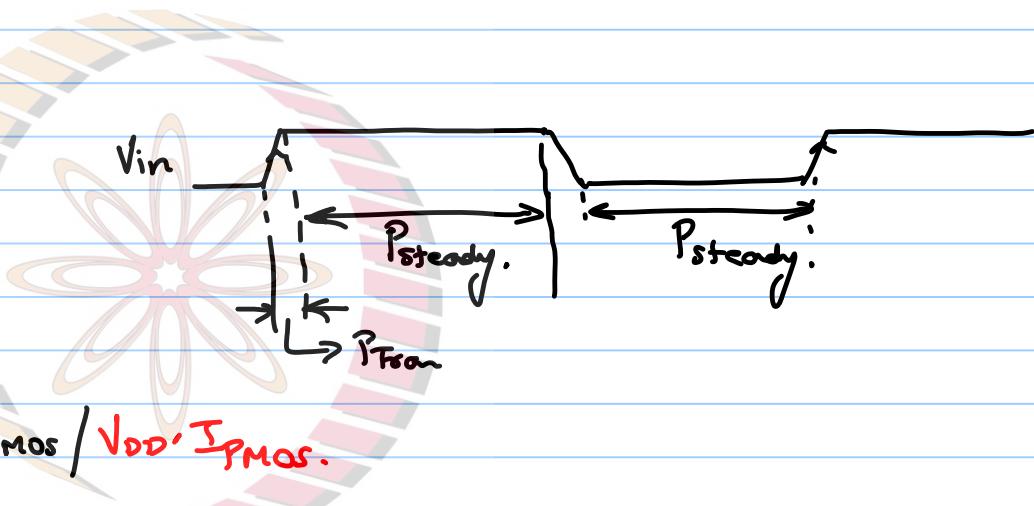
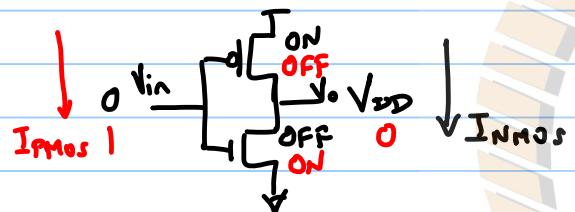
$$P_{sc} = \alpha E_{sc} \cdot f_{CLK}$$

$$= \alpha \cdot I_p (V_{DD} - 2V_{Th}) \cdot t_{rise} \cdot f_{CLK}$$

Transient Power = $P_{DNW} + P_{CC} = \alpha f_{CLK} \cdot (C_L V_{DD}^2 + I_p (V_{DD} - 2V_{Th}) t_{rise})$

↑ ↑
Reduce f_{CLK} to reduce $P_{Trans.}$ Dominate

LEAKAGE POWER



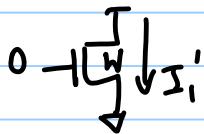
$$\text{POWER FROM } V_{DD} = \sqrt{V_{DD}} \cdot I_{NMOS} / \sqrt{V_{DD}} \cdot I_{PPMOS}$$

$$\text{Ave Pow} = \sqrt{V_{DD}} (I_{NMOS} + I_{PPMOS})$$

$$I_{NMOS} = \frac{W}{L} I_s e^{\frac{(V_{ds}-V_{tn})}{n \cdot k_t}} (1 - e^{-\frac{V_{ds}}{d_t}})$$

STACKING EFFECT

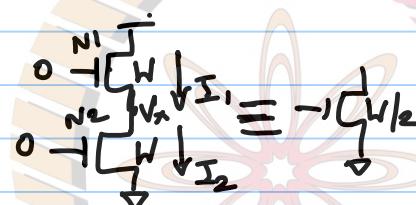
1-STACK



(a)

$$\boxed{I_1 = I_2}$$

2-STACK.



(b)

N ₁	V _{GS}	V _{DS}
N ₂	-V _X	V _{DD} - V _X
	0	V _X

- ASSUME:
- 1) NO BODY EFFECT ($V = 0$)
 - 2) NO DIBL ($\eta = 0$)
 - 3) V_{DD} IS LARGE
 - 4) IDEALITY FACTOR = $n = 1$

$$I_1 = \frac{W \cdot I_0}{L} e^{\frac{-V_x - V_{Tn}}{qT}}$$

$$I_2 = \frac{W}{L} I_0 e^{\left(\frac{-V_{Tn}}{qT}\right)} \left(1 - e^{\frac{-V_x}{qT}}\right)$$

N₂: LARGE V_{GS} ($0/$) $\Rightarrow V_{DS}$ is SMALL

N₁: SMALL V_{GS} (-V_X) $\Rightarrow V_{DS}$ is LARGE

$\Rightarrow V_x$ CLOSER TO GND.

$$I_1 = I_2$$

$$\Rightarrow \frac{V_x}{L} e^{\frac{-V_{Tn}}{Rt}} = \frac{V_x}{L} e^{\frac{-V_{Tn}}{Rt}} (1 - e^{-V_x/Rt})$$

$$\Rightarrow V_x = \phi_t \ln(z)$$

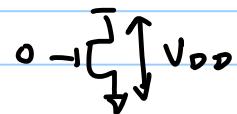
$$I_1 = \frac{W}{L} \cdot I_0 e^{\frac{(-\phi_t \ln(z) - V_{Tn})}{Rt}}$$

$$\therefore I_1 = \frac{L(W)}{2(L)} \cdot I_0 e^{\frac{-V_{Tn}}{Rt}}$$

$$I_1' = \frac{W}{L} \cdot I_0 e^{-\frac{V_{Tn}}{Rt}}$$

$$-1 \begin{bmatrix} \frac{1}{2} \\ \frac{1}{2} \end{bmatrix} \quad 1 \begin{bmatrix} \frac{1}{2} \\ \frac{1}{2} \end{bmatrix}$$

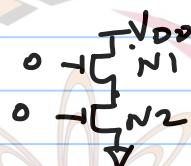
V_{TH} DIBL



DIBL EFFECT ON

$$V_{TH} = \eta V_{DD}$$

$$\downarrow V_{Th}$$



DIBL EFFECT ON

$$N_1 = \eta (V_{DD} - V_x)$$

NPTEL